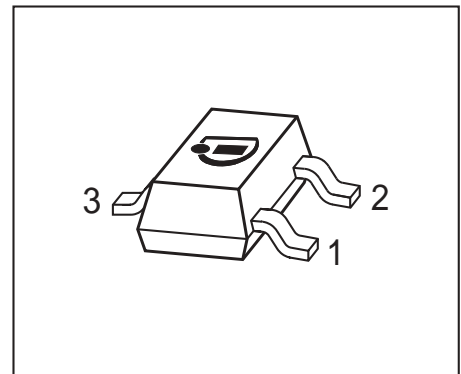


**Silicon N-Channel MOSFET Triode**

- For high-frequency stages up to 300 MHz preferably in FM applications
- Pb-free (RoHS compliant) package<sup>1)</sup>
- Qualified according AEC Q101



**ESD (Electrostatic discharge) sensitive device, observe handling precaution!**

Type	Marking	Pin Configuration						Package
BF999	LBs	1=G	2=D	3=S	-	-	-	SOT23

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Drain-source voltage	$V_{DS}$	20	V
Continuous drain current	$I_D$	30	mA
Gate-source peak current	$\pm I_{GSM}$	10	mA
Total power dissipation $T_S \leq 76 \text{ }^\circ\text{C}$	$P_{tot}$	200	mW
Storage temperature	$T_{stg}$	-55 ... 150	°C
Channel temperature	$T_{ch}$	150	

**Thermal Resistance**

Parameter	Symbol	Value	Unit
Channel - soldering point <sup>2)</sup>	$R_{thchs}$	$\leq 370$	K/W

<sup>1</sup>Pb-containing package may be available upon special request

<sup>2</sup>For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

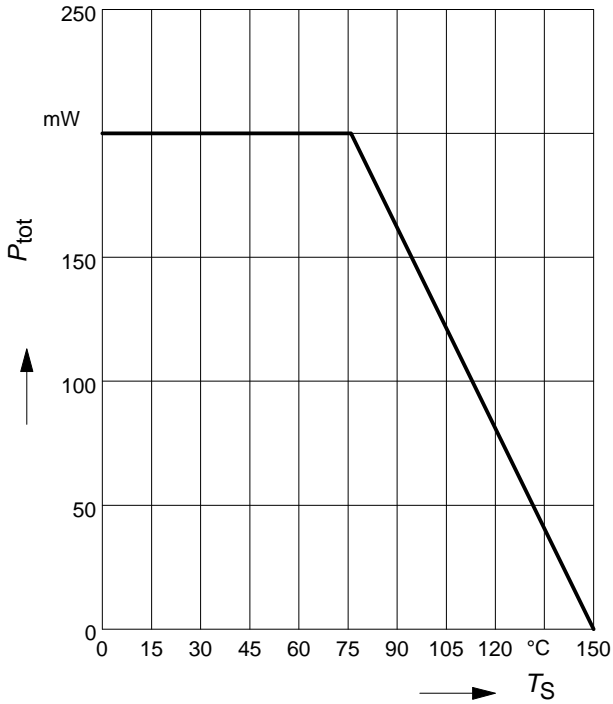
**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC Characteristics</b>					
Drain-source breakdown voltage $I_D = 10 \mu\text{A}, -V_{GS} = 4 \text{ V}$	$V_{(BR)DS}$	20	-	-	V
Gate-source breakdown voltage $\pm I_{GS} = 10 \text{ mA}, V_{DS} = 0$	$\pm V_{(BR)GSS}$	6.5	-	12	
Gate-source leakage current $\pm V_{GS} = 5 \text{ V}, V_{DS} = 0$	$\pm I_{GSS}$	-	-	50	nA
Drain current $V_{DS} = 10 \text{ V}, V_{GS} = 0$	$I_{DSS}$	5	10	16	mA
Gate-source pinch-off voltage $V_{DS} = 10 \text{ V}, I_D = 20 \mu\text{A}$	$-V_{GS(p)}$	-	0.8	1.5	V

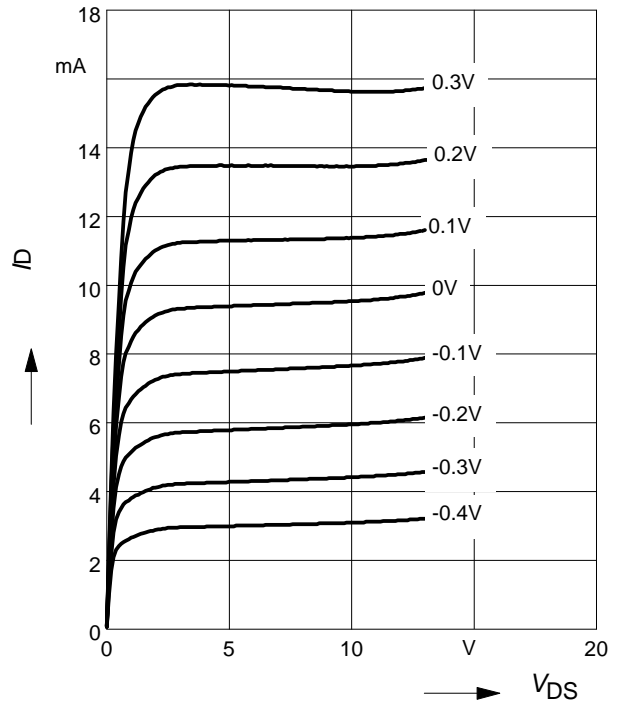
**Electrical Characteristics at  $T_A = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>AC Characteristics</b>					
Forward transconductance $V_{DS} = 10 \text{ V}, I_D = 10 \text{ mA}$	$g_{fs}$	14	20	-	mS
Gate input capacitance $V_{DS} = 10 \text{ V}, I_D = 10 \text{ mA}, f = 10 \text{ MHz}$	$C_{gss}$	-	2.5	-	pF
Output capacitance $V_{DS} = 10 \text{ V}, I_D = 10 \text{ mA}, f = 10 \text{ MHz}$	$C_{dss}$	-	0.9	-	pF
Power gain $V_{DS} = 10 \text{ V}, I_D = 10 \text{ mA}, f = 45 \text{ MHz}$	$G_p$	-	27	-	dB
Noise figure $V_{DS} = 10 \text{ V}, I_D = 10 \text{ mA}, f = 45 \text{ MHz}$	$F$	-	2.1	-	dB

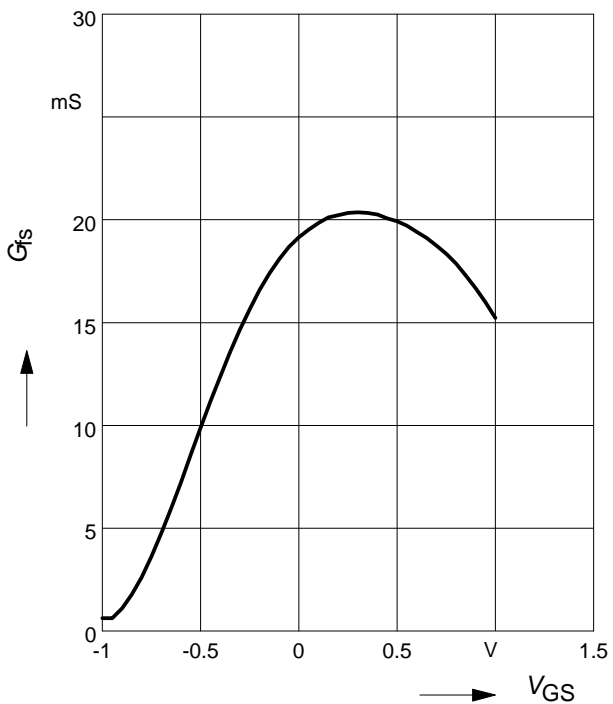
**Total power dissipation  $P_{tot} = f(T_S)$**



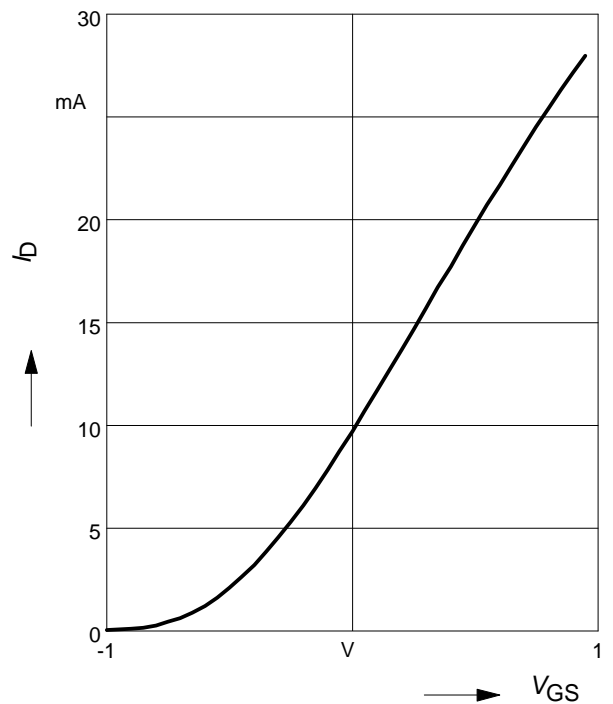
**Output characteristics  $I_D = f(V_{DS})$**



**Gate transconductance  $g_{fs} = f(V_{GS})$**

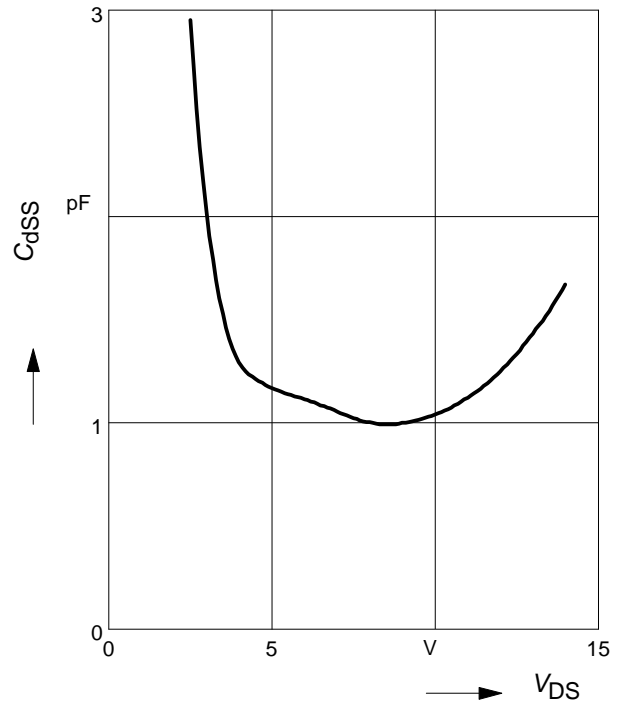
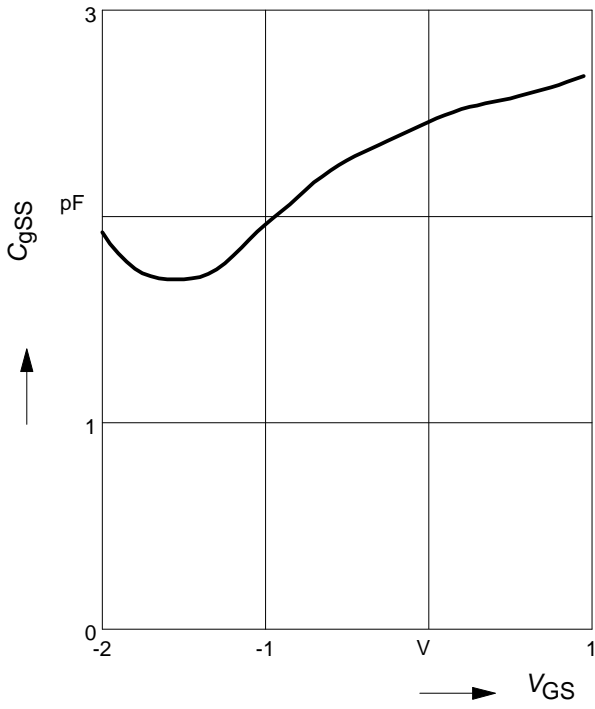


**Drain current  $I_D = f(V_{GS})$**

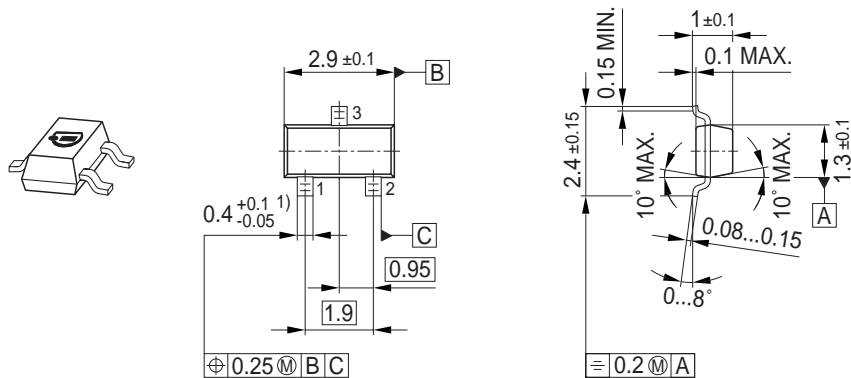


Gate input capacitance  $C_{gss} = f(V_{GS})$

Output capacitance  $C_{dss} = f(V_{DS})$

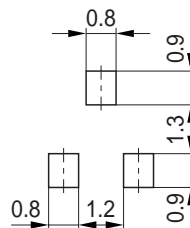


Package Outline

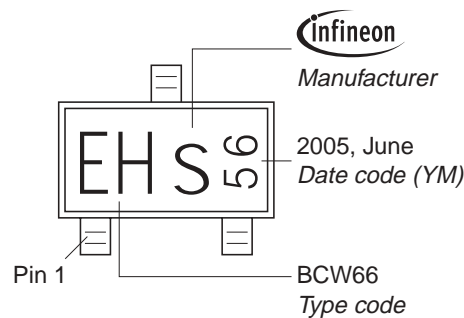


1) Lead width can be 0.6 max. in dambar area

Foot Print

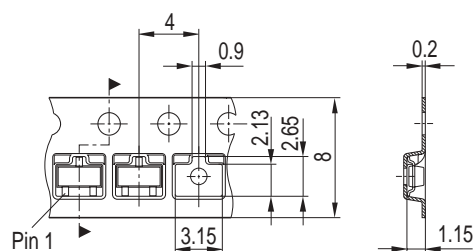


Marking Layout (Example)



Standard Packing

Reel  $\varnothing$ 180 mm = 3.000 Pieces/Reel  
 Reel  $\varnothing$ 330 mm = 10.000 Pieces/Reel



Edition 2006-02-01

Published by

Infineon Technologies AG

81726 München, Germany

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